

INFORMATION DISCLOSURE CITATION
 (Use several sheets if necessary)

Docket Number (Optional)

T36-163905M/RS

Application Number

10/725,380

Applicant(s)

Naoki Shibata, et al.

Filing Date

12/03/03

Group Art Unit

2818

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	REF	DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE

FOREIGN PATENT DOCUMENTS

	REF	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	Translation	
							YES	NO
DV		02-081482	03/22/1990	JAPAN			ABS	

OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)

DV		Japanese Office Action dated December 14, 2004 with English translation.
DV		Heon Lee, et al. Growth of Thick GaN Films on RF Sputtered AlN Buffer Layer by Hydride Vapor Phase Epitaxy, Journal of Electric Materials, vol 26, No. 8 (1997) pp 898-902.

EXAMINER

ghilard

DATE CONSIDERED

03/22/05

EXAMINER: Initial if citation considered, whether or not citation is in conformance with MPEP Section 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.